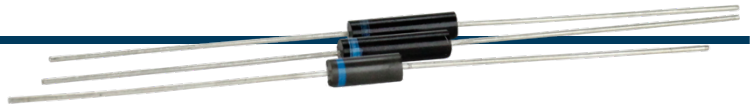
HVEF SERIES

8 to 12kV, 20 to 30mA, 20nS
Axial Lead Low Current Diodes



Features

- Ultra-Fast Reverse Recovery Time
- Miniature Package
- Molded Plastic Body, ANSI/UL94 V-0 Rated Material

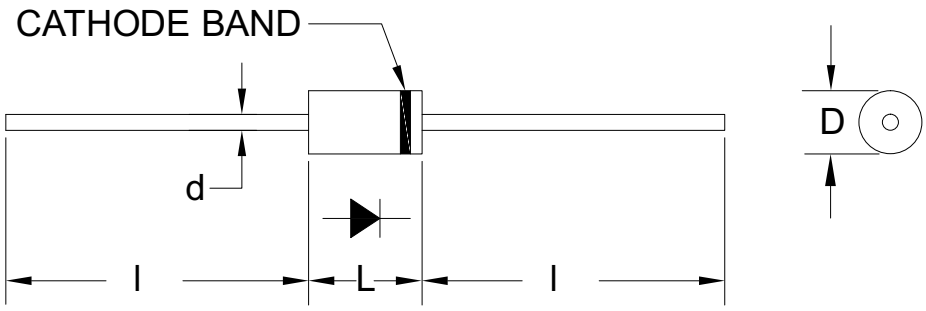
Specifications[1]

Part Number	V_{RRM} V	I_{FAVM} mA	V_F V	I_R µA	I_{FSM} A	C_J pF	T_{RR} nS	L in.	D in.	d in.	l in.
HVEF8P	8000	30	20	0.2	3	0.33	20	0.26	0.1	0.021	1.0
HVEF10P	10000	20	23	0.2	3	0.30	20	0.40	0.1	0.021	1.0
HVEF12P	12000	20	27	0.2	3	0.25	20	0.40	0.1	0.021	1.0

Temperature °C	
Operating Temperature	-55 to 125
Storage Temperature	-55 to 175
Maximum Junction Temperature	125

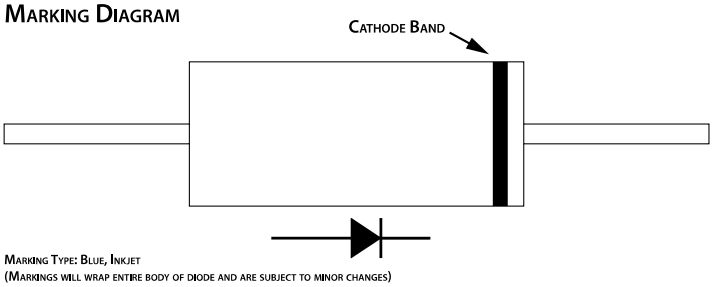
[1]25°C ambient temperature unless stated otherwise.

Drawings



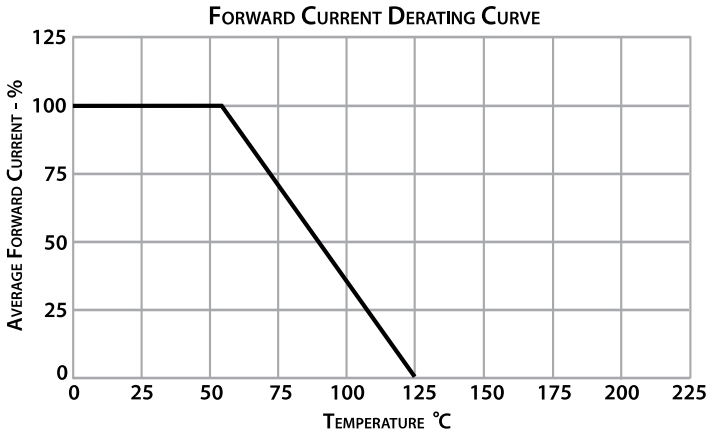
Dimensions in inches, tolerances ±0.020 except as noted

Marking Diagram



Marking Type: Blue, Inkjet
(Markings will wrap entire body of diode and are subject to minor changes)

Forward Current Derating Curve



Specification Definitions

	Specifications	Conditions
V_{RRM}	Maximum Repetitive Reverse Voltage	-
I_{FAVM}	Maximum Average Forward Current	At T_A = 55°C
V_F	Maximum Forward Voltage Drop	At I_F = 5mA
I_R	Maximum Leakage Current	At V_{RRM}
I_{FSM}	Maximum Surge Current	At 8.3mS, Single Half Sine
C_J	Typical Junction Capacitance	At V_R = 0VDC, f = 1MHz
T_{RR}	Maximum Reverse Recovery Time	I_F = 2mA; I_R = -4mA; I_{RR} = -1mA

Note: Specifications subject to change without notice. Photo is representation only.

RoHS COMPLIANT